Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-9. (Canceled)

10. (Withdrawn) A method for protecting circuit device materials, comprising:

placing a reactive material on an interior surface of the device;

placing a meltable material upon the reactive material to substantially cover the reactive material; and

in response to an application of energy to the meltable material, removing at least a portion of the meltable material, the removing exposing at least a portion of the reactive material.

11. (Withdrawn) The method of claim 10 wherein:

the circuit device comprises an optoelectronic devices and includes an active area;

the removing step includes heating the meltable material to a temperature in the range of 75 to 300 degrees Celsius, and the removing step further comprises covering substantially all of the active area with the meltable material.

12. (Withdrawn) The method of claim 10 further comprising sealing the device and wherein at least one of the shape and activity of the getter is modified after the sealing of the device.

13-17. (Canceled)

18. (Withdrawn) A cap including a getter, the cap comprising:

a reactive material disposed on a cap surface; and

an inert material placed to cover more than approximately fifty percent of the reactive material, the inert material adapted to flow in response to application of energy to the inert material.

19. (Withdrawn) The cap of claim 18, wherein the cap includes an interior surface having a recessed portion.

20. (Withdrawn) The cap of claim 19, wherein:

the inert material covers at least some of the recessed portion; and

in response to the application of energy, the inert material melts.

21. (Withdrawn) The cap of claim 19, wherein the inert material covers less than the entire recessed portion thereby leaving a cavity between the inert material and at least one sidewall of the recessed portion.

22. (Currently Amended) A getter composition, comprising:

a reactive material disposed in an encapsulated device, the reactive material comprising one or more of barium oxide, calcium oxide, calcium or barium ~~substantially more reactive than at least one device material to: matter desorbed from at least one surface of the device, matter from a space within the device, and matter permeating into the space within the device from outside the device~~; and

an inert material disposed in the encapsulated device, the inert material adapted to respond to energy input by at least one of: melting, phase change, or morphological change.

23. (Currently Amended) The composition of claim 22 wherein:

~~the reactive material comprises an activated powder containing at least one of activated alumina, silica, zeolite, barium oxide, calcium oxide, calcium, and barium; and~~

the inert material comprises at least one of paraffin wax, low-density polyethylene, ~~or~~ Elvax® resin, a polyolefin resin wax, a microcrystalline wax, a silicon resin wax, an ester wax, a polyurethane wax, an acrylate or a polyamide.

24. (Currently Amended) The composition of claim ~~23~~ 22 wherein the inert material comprises a binder and the ~~activated powder~~ reactive material is mixed with the binder~~, the activated material substantially dispersed in the binder~~.

25. (New) The composition of claim 24, wherein the reactive material is substantially dispersed in the binder.

26. (New) The composition of claim 22, wherein the weight fraction of the reactive material in the inert material is between about 10% and 90%.

27. (New) The composition of claim 22, wherein the reactive material has a particle size range of about 0.1 to about 200 micrometers.

28. (New) The composition of claim 27, wherein the reactive material has a particle size range of about 0.3 to about 50 micrometers.

29. (New) The composition of claim 22, wherein the encapsulated device is an encapsulated optoelectronic device.

30. (New) The composition of claim 29, wherein the encapsulated optoelectronic device is an encapsulated organic light emitting diode.

31. (New) The composition of claim 22, wherein the reactive material is in a layer.

32. (New) The composition of claim 31, wherein the layer has a thickness in the range of about 0.1 to about 10 microns.

33. (New) The composition of claim 22, wherein the inert material is a wax.

34. (New) The composition of claim 22, wherein the inert material is Elvax® resin.

35. (New) A getter structure, comprising:

a first layer of a reactive material disposed in an encapsulated device, the reactive material substantially more reactive than at least one device material to: matter desorbed from at least one surface of the device, matter from a space within the device, and matter permeating into the space within the device from outside the device; and

a second layer of an inert material disposed on the first layer, the inert material adapted to respond to energy input by at least one of: melting, phase change, or morphological change.

36. (New) The composition of claim 35, wherein the first layer comprises at least one of activated alumina, silica, zeolite, barium oxide, calcium oxide, calcium, and barium.

37. (New) The composition of claim 35, wherein the first layer has a thickness in the range of about 0.1 to about 10 microns.

38. (New) The composition of claim 35, wherein the second layer comprises at least one of paraffin wax, low-density polyethylene, Elvax® resin, a polyolefin resin wax, a microcrystalline wax, a silicon resin wax, an ester wax, a polyurethane wax, an acrylate or a polyamide.